

Ultrafast Rectifier

MUR5060PT

FEATURES

- Guarding for over voltage protection
- Dual rectifier construction, positive center tap
- Metal of silicon rectifier, majority carrier conduction
- Low forward voltage, high efficiency
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

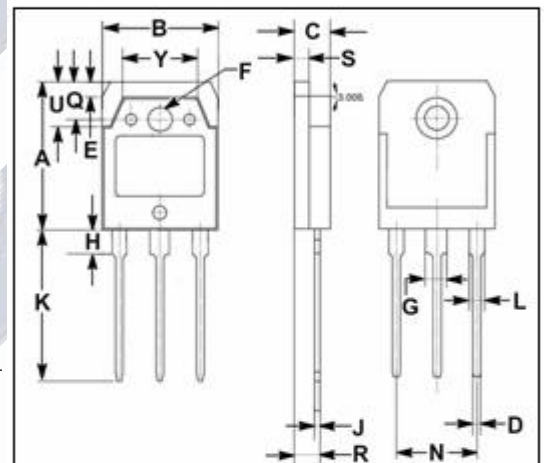
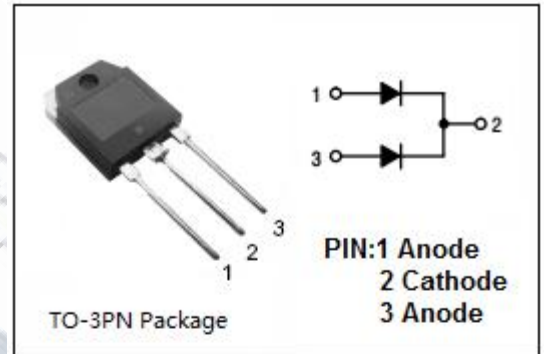
APPLICATIONS

- Uninterruptible power supplies
- Rectifier in switch mode power supplies
- Ultrasonic cleaners and welders

Downloaded from Alldatasheet.com

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{RRM} V _{RWM} V _R	Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	600	V
I _{F(AV)}	Average Rectified Forward Current	50	A
I _{FSM}	Nonrepetitive Peak Surge Current (Surge applied at rated load conditions half-wave, single phase, 60Hz)	340	A
P _D	Maximum power dissipation	125	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-40~150	°C



DIM	mm	
	MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

Fast Recovery Rectifier

MUR5060PT

ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$) (Pulse Test: Pulse Width=300 μ s,Duty Cycle \leq 2%)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Maximum Instantaneous Forward Voltage	$I_F=25\text{A}; T_j=25^\circ\text{C}$	1.6	V
I_R	Maximum Instantaneous Reverse Current	$V_R=V_{RWM}; T_j=25^\circ\text{C}$	1	μ A
t_{rr}	Maximum Reverse Recovery Time	$I_F=0.5\text{A}; I_R=1\text{A}; I_{rr}=0.25\text{A}$	50	ns